

### SWITCHING P-CHANNEL POWER MOS FET

#### DESCRIPTION

The 2SJ598 is P-channel MOS Field Effect Transistor designed for solenoid, motor and lamp driver.

#### FEATURES

- Low on-state resistance:  
 $R_{DS(on)1} = 130 \text{ m}\Omega \text{ MAX. (} V_{GS} = -10 \text{ V, } I_D = -6 \text{ A)}$   
 $R_{DS(on)2} = 190 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.0 \text{ V, } I_D = -6 \text{ A)}$
- Low  $C_{iss}$ :  $C_{iss} = 720 \text{ pF TYP.}$
- Built-in gate protection diode
- TO-251/TO-252 package

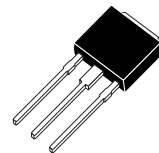
#### ★ ORDERING INFORMATION

PART NUMBER	PACKAGE
2SJ598	TO-251 (MP-3)
2SJ598-Z	TO-252 (MP-3Z)

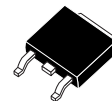
#### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

Drain to Source Voltage ( $V_{GS} = 0 \text{ V}$ )	$V_{DSS}$	-60	V
Gate to Source Voltage ( $V_{DS} = 0 \text{ V}$ )	$V_{GSS}$	$\mp 20$	V
Drain Current (DC) ( $T_C = 25^\circ\text{C}$ )	$I_{D(DC)}$	$\mp 12$	A
Drain Current (pulse) <sup>Note1</sup>	$I_{D(pulse)}$	$\mp 30$	A
Total Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_T$	23	W
Total Power Dissipation ( $T_A = 25^\circ\text{C}$ )	$P_T$	1.0	W
Channel Temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$
Single Avalanche Current <sup>Note2</sup>	$I_{AS}$	-12	A
Single Avalanche Energy <sup>Note2</sup>	$E_{AS}$	14.4	mJ

(TO-251)



(TO-252)



**Notes 1.**  $PW \leq 10 \mu\text{s}$ , Duty Cycle  $\leq 1\%$

**2.** Starting  $T_{ch} = 25^\circ\text{C}$ ,  $V_{BD} = -30 \text{ V}$ ,  $R_G = 25 \Omega$ ,  $V_{GS} = -20 \rightarrow 0 \text{ V}$

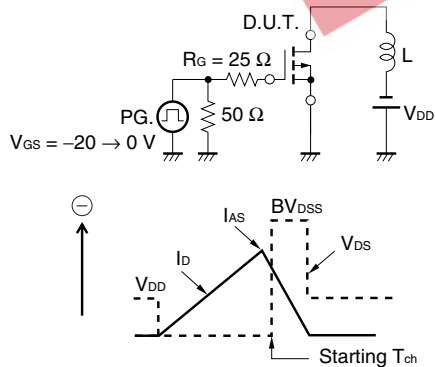
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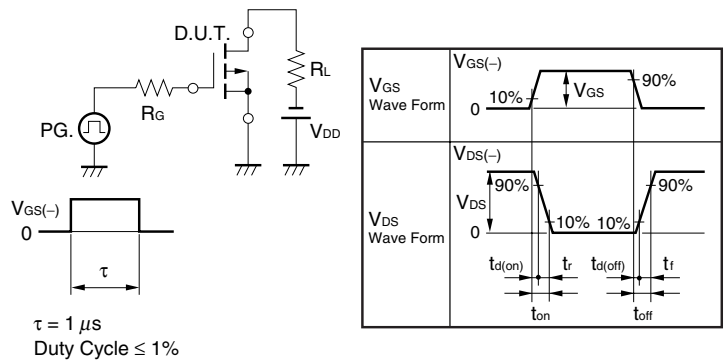
**ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -60V, V_{GS} = 0V$			-10	$\mu A$
Gate Leakage Current	$I_{GSS}$	$V_{GS} = \mp 16V, V_{DS} = 0V$			$\mp 10$	$\mu A$
Gate Cut-off Voltage	$V_{GS(off)}$	$V_{DS} = -10V, I_D = -1mA$	-1.5	-2.0	-2.5	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = -10V, I_D = -6A$	5	11		S
Drain to Source On-state Resistance	$R_{DS(on)1}$	$V_{GS} = -10V, I_D = -6A$		102	130	m $\Omega$
	$R_{DS(on)2}$	$V_{GS} = -4.0V, I_D = -6A$		131	190	m $\Omega$
Input Capacitance	$C_{iss}$	$V_{DS} = -10V$		720		pF
Output Capacitance	$C_{oss}$	$V_{GS} = 0V$		150		pF
Reverse Transfer Capacitance	$C_{rss}$	$f = 1MHz$		50		pF
Turn-on Delay Time	$t_{d(on)}$	$I_D = -6A$		7		ns
Rise Time	$t_r$	$V_{GS} = -10V$		4		ns
Turn-off Delay Time	$t_{d(off)}$	$V_{DD} = -30V$		35		ns
Fall Time	$t_f$	$R_G = 0\Omega$		10		ns
Total Gate Charge	$Q_G$	$I_D = -12A$		15		nC
Gate to Source Charge	$Q_{GS}$	$V_{DD} = -48V$		3		nC
Gate to Drain Charge	$Q_{GD}$	$V_{GS} = -10V$		4		nC
Body Diode Forward Voltage	$V_{F(S-D)}$	$I_F = 12A, V_{GS} = 0V$		0.98		V
Reverse Recovery Time	$t_{rr}$	$I_F = 12A, V_{GS} = 0V$		50		ns
Reverse Recovery Charge	$Q_{rr}$	$di/dt = 100A/\mu s$		100		nC

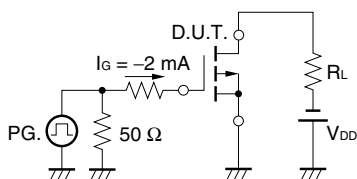
**TEST CIRCUIT 1 AVALANCHE CAPABILITY**



**TEST CIRCUIT 2 SWITCHING TIME**

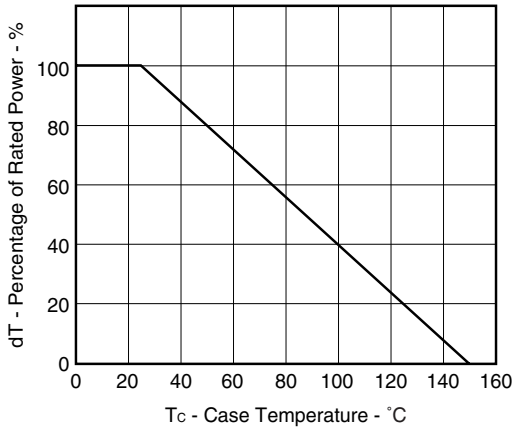


**TEST CIRCUIT 3 GATE CHARGE**

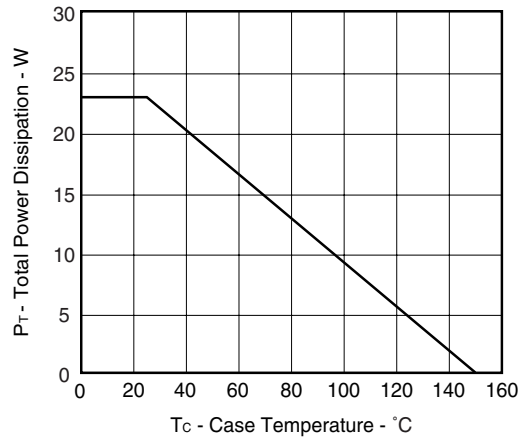


TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)

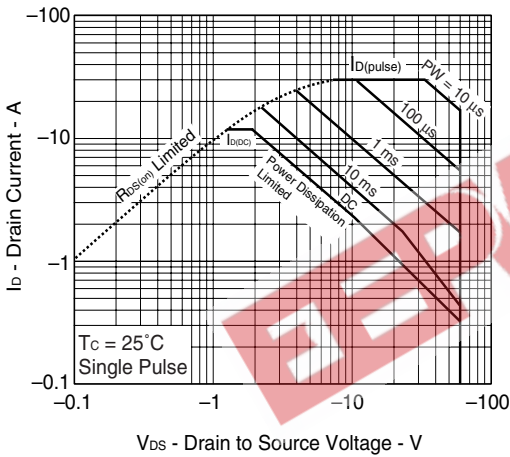
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



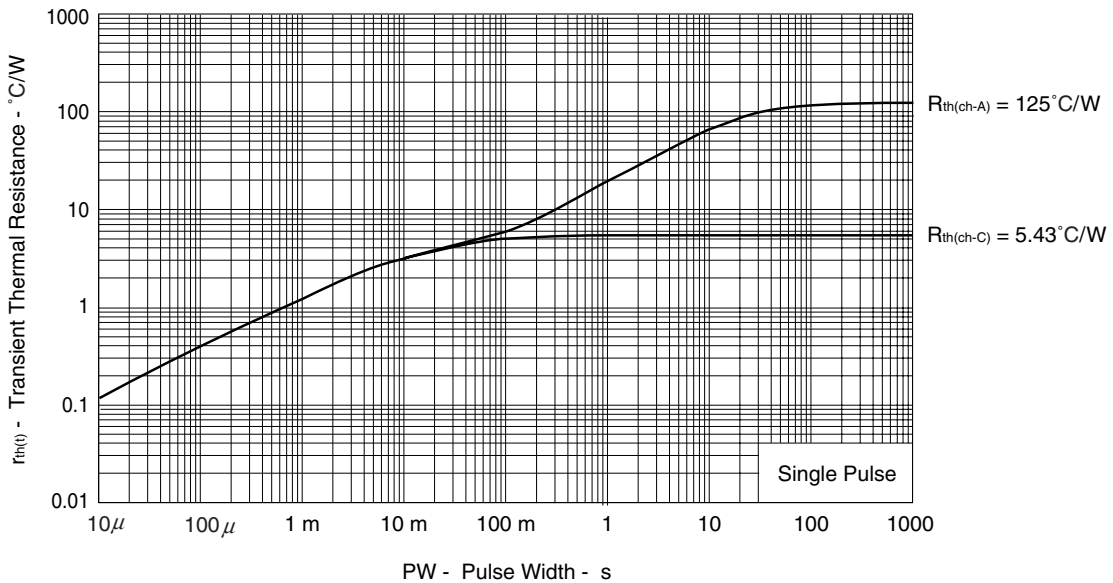
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



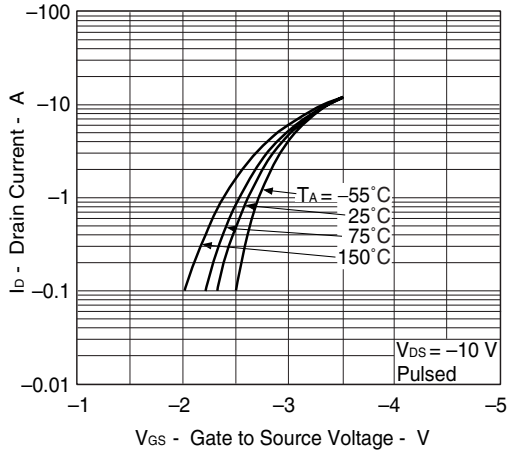
FORWARD BIAS SAFE OPERATING AREA



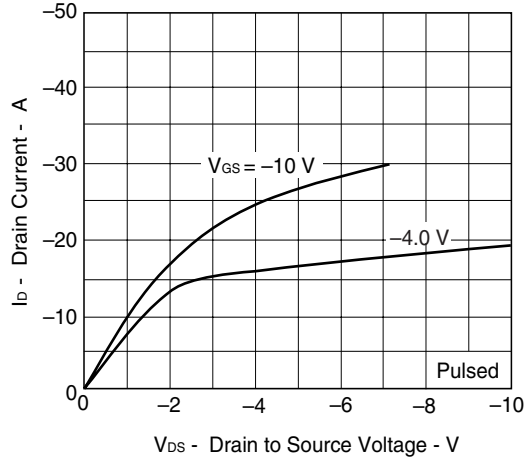
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



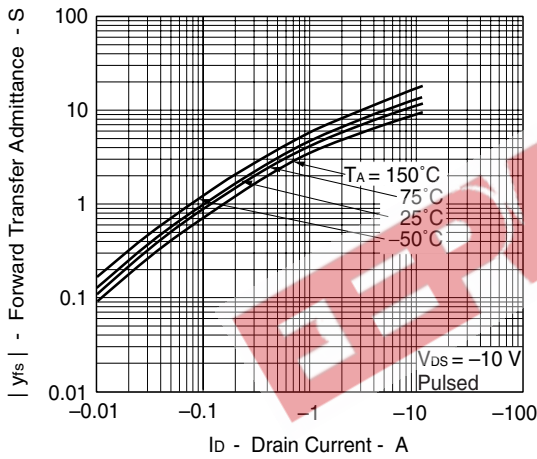
FORWARD TRANSFER CHARACTERISTICS



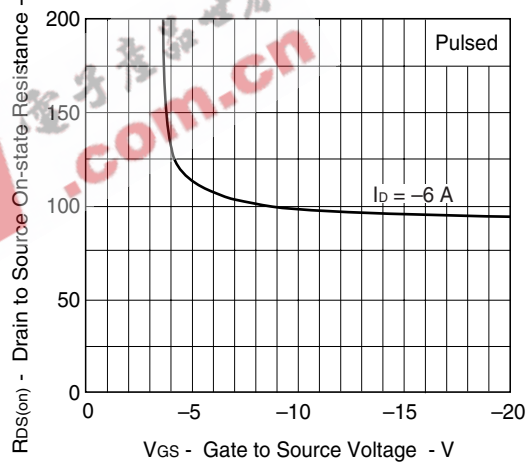
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



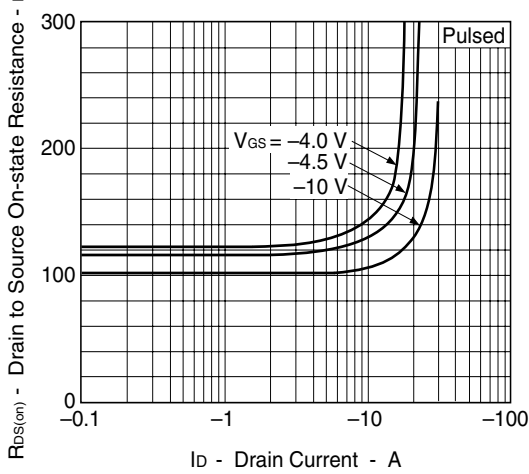
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



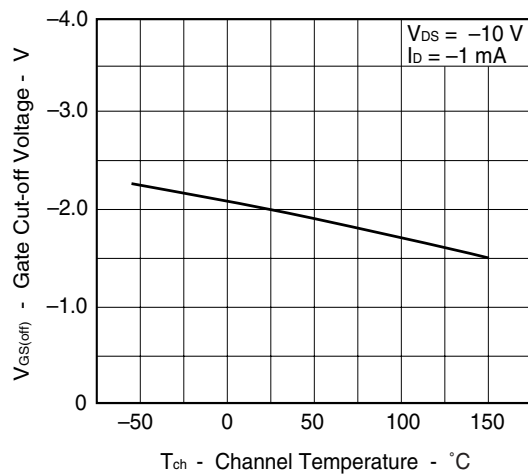
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

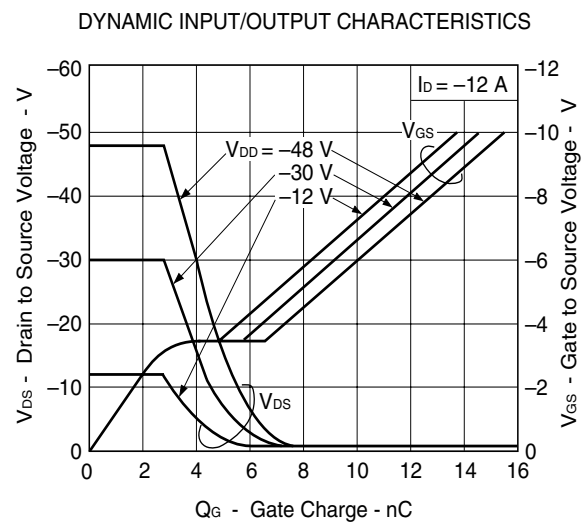
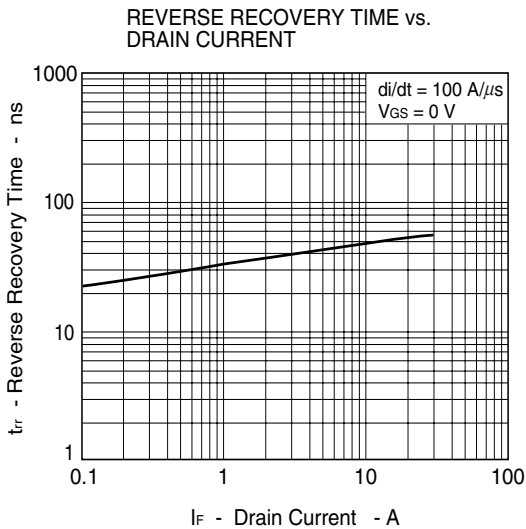
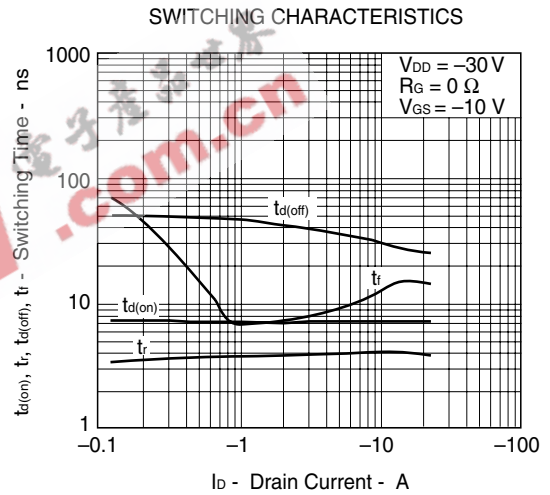
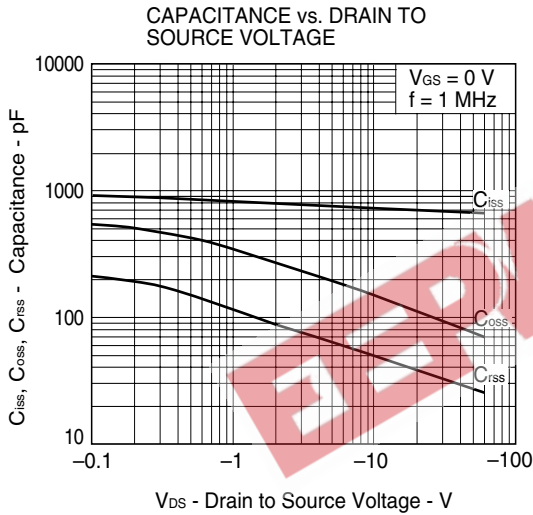
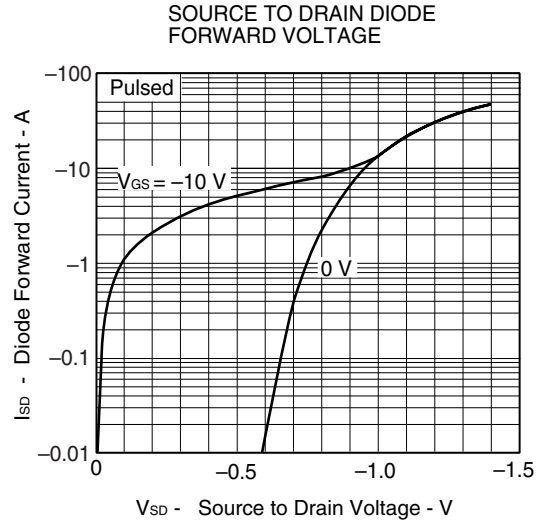
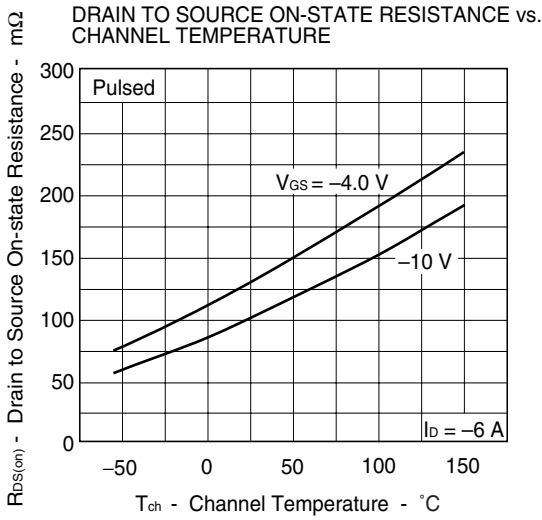


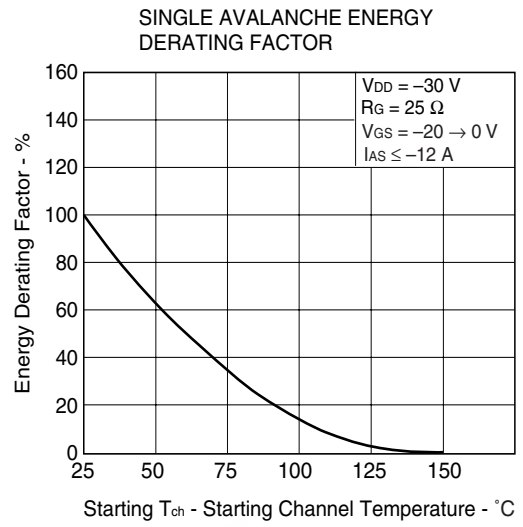
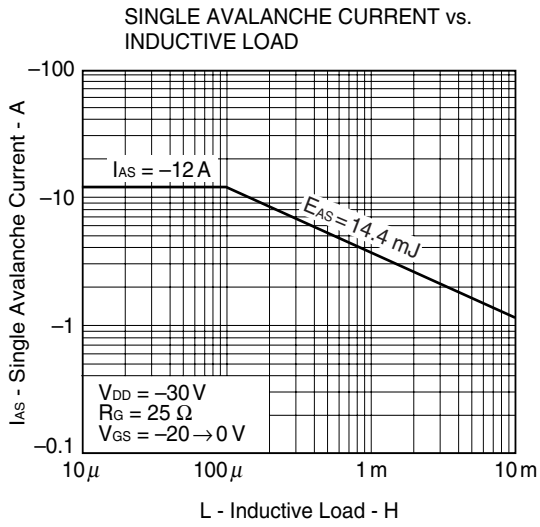
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



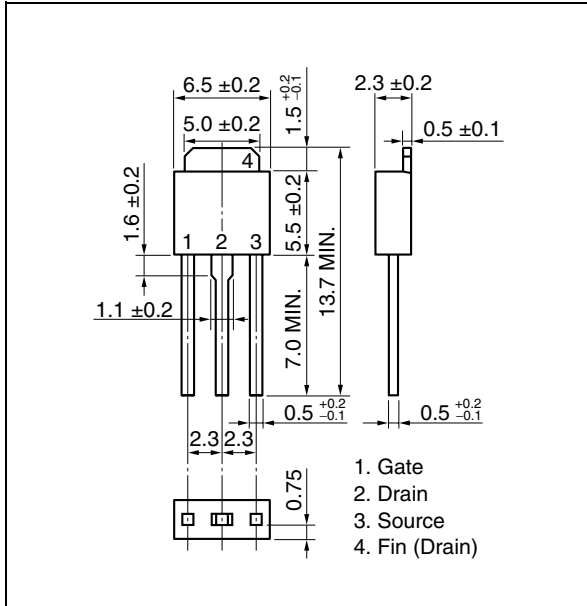




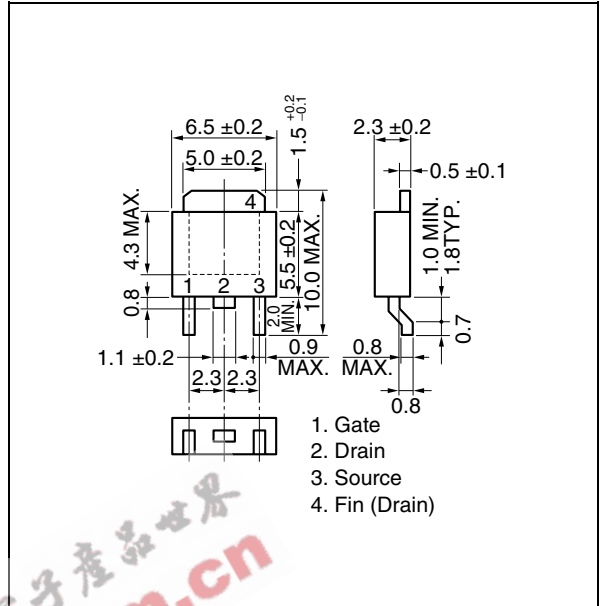
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★ PACKAGE DRAWINGS (Unit: mm)

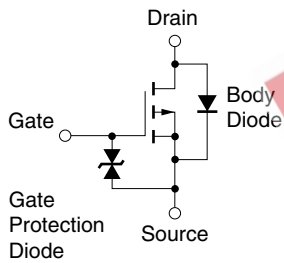
1) TO-251 (MP-3)



2) TO-252 (MP-3Z)



EQUIVALENT CIRCUIT



**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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